Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

- 1. (Original) A thin film transistor comprising:
 - an insulating layer having a first opening;
 - a first conductive layer in the opening; and
 - a second conductive layer on the insulating layer and the first conductive layer,
 - wherein the first conductive layer is wider and thicker than the second conductive

layer.

- 2. (Original) A thin film transistor comprising:
 - an insulating layer having a first opening;
 - a first conductive layer in the opening; and
 - a second conductive layer on the insulating layer and the first conductive layer,
- wherein the first conductive layer is wider and thicker than the second conductive

layer, and

wherein the second conductive layer is formed by a droplet discharge method using a conductive material.

- 3. (Original) A display device comprising:
 - a first insulating layer having a first opening;
 - a first conductive layer in the first opening;
 - a second conductive layer on the first insulating layer and the first conductive layer;
- a semiconductor layer over the second conductive layer with a gate insulating film therebetween;
 - a third conductive layer over the semiconductor layer;
 - a second insulating layer having a second opening over the third conductive layer; and
 - a fourth conductive layer in the second opening,
- wherein the first conductive layer is wider and thicker than the second conductive layer, and

wherein the fourth conductive layer is thicker than the third conductive layer.

- 4. (Currently Amended) A display device comprising:
 - a first insulating layer having a first opening;
 - a first conductive layer in the first opening;
- a second conductive layer on the first insulating layer and the first insulating layer and the first conductive layer;
- a semiconductor layer over the second conductive layer with a gate insulting film therebetween;
 - a third conductive layer over the semiconductor layer;
 - a second insulating layer having a second opening over the third conductive layer; and
 - a fourth conductive layer in the second opening,
- wherein the first conductive layer is wider and thicker than the second conductive layer,
- wherein the fourth conductive layer is thicker than the third conductive layer, and wherein each of the second conductive layer and the third conductive layer is formed by a droplet discharge method using a conductive material.
- 5. (Original) A display device comprising:
 - a first insulating layer having a first opening;
 - a first conductive layer in the first opening;
 - a second conductive layer on the first insulating layer and the first conductive layer;
- a semiconductor layer over the second conductive layer with a gate insulating film therebetween;
 - a pair of third conductive layers over the semiconductor layer;
 - a first electrode over one of the pair of third conductive layers;
 - an electroluminescent layer over the first electrode; and
- a second electrode over the electroluminescent layer,
- wherein the first conductive layer is wider and thicker than the second conductive layer.

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6. (Original) A display device comprising

- a first insulating layer having a first opening;
- a first conductive layer in the first opening;
- a second conductive layer on the first insulating layer and the first conductive layer;
- a semiconductor layer over the second conductive layer with a gate insulating film therebetween;
 - a pair of third conductive layers over the semiconductor layer;
 - a first electrode over one of the pair of third conductive layers;
 - an electroluminescent layer over the first electrode; and
 - a second electrode over the electroluminescent layer,
- wherein the first conductive layer is wider and thicker than the second conductive layer, and

wherein the second conductive layer is formed by a droplet discharge method using a conductive material.

7. (Original) A display device comprising:

- a first insulating layer having a first opening;
- a first conductive layer in the first opening;
- a second conductive layer on the insulating layer and the first conductive layer;
- a semiconductor layer over the second conductive layer with a gate insulating film therebetween;
 - a pair of third conductive layers over the semiconductor layer;
 - a first electrode over one of the pair of third conductive layers;
- a second insulating layer having a second opening over the other one of the pair of third conductive layers;
 - a fourth conductive layer in the second opening;
 - an electroluminescent layer over the first electrode; and
 - a second electrode over the electroluminescent layer,
- wherein the first conductive layer is wider and thicker than the second conductive layer, and

wherein the fourth conductive layer is thicker than the third conductor layer.

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- 8. (Original) A display device comprising:
 - a first insulating layer having a first opening;
 - a first conductive layer in the first opening;
 - a second conductive layer on the first insulating layer and the first conductive layer;
- a semiconductor layer over the second conductive layer with a gate insulating film therebetween;
 - a pair of third conductive layers over the semiconductor layer;
 - a first electrode over one of the pair of third conductive layers;
- a second insulating layer having a second opening over the other one of the pair of third conductive layers;
 - a fourth conductive layer in the second opening;
 - an electroluminescent layer over the first electrode; and
 - a second electrode over the electroluminescent layer,
- wherein the first conductive layer is wide and thicker than the second conductive layer,
- wherein the fourth conductive layer is thicker than the third conductive layer, and wherein each of the second conductive layer and the third conductive layer is formed by a droplet discharge method using a conductive material.
- 9. (Original) The thin film transistor or the display device according to any one of claims 1 to 8, wherein the thin film transistor or the display device further comprises a titanium oxide film below the first conductive layer.
- 10. (Original) The thin film transistor or the display device according to any one of claims 1 to 8, wherein the thin film transistor or the display device further comprises a film comprising at least one selected from the group consisting of W (tungsten), Al (aluminum), Ta (tantalum), Zr (zirconium), Hf (hafnium), Ir (iridium), Nb (niobium), Pd (lead), Pt (platinum), Mo (molybdenum), Rh (rhodium), Sc (scandium), Ti (titanium), V (vanadium), Cr (chromium), Mn (manganese), Fe (iron), Co (cobalt), Ni (nickel), Cu (copper), and Zn (zinc) below the first conductive layer.

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11. (Original) The thin film transistor or the display device according to any one of claims 1

to 8, wherein the second conductive layer includes at least one of silver, gold, copper, and

indium tin oxide.

12. (Original) The display device according to any one of claims 3 to 8, wherein the third

conductive layer includes at least one of silver, gold, copper, and indium tin oxide.

13. (Original) The thin film transistor or the display device according to any one of claims 1

to 8, wherein a width of the first opening is from 5 μ m to 100 μ m.

14. (Original) The display device according to any one of claims 3 to 8, wherein the

semiconductor layer is an amorphous semiconductor layer including at least one of hydrogen

and halogen.

15. (Currently Amended) The display device according to any one of claims 3 to 8, wherein

the semiconductor layer is an amorphous a semi-amorphous semiconductor layer including at

least one of hydrogen and halogen.

16. (Original) The display device according to any one of claims 3 to 8, wherein the

semiconductor layer is a polycrystalline semiconductor including at least one of hydrogen

and halogen.

17. (Original) The display device according to any one of claims 3 to 8, wherein a channel

length of the semiconductor layer is from 5 μm to 100 μm.

18. (Original) A television apparatus including the display device according to any one of

claims 3 to 8 as a display screen.

19. (Original) A television apparatus including a display device with the thin film transistor

according to claims 1 or 2 as a display screen.

20-32. (Canceled)

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